AMENDMENTS TO THE CLAIMS

1-13. (Cancelled)

14. (Currently Amended) A semiconductor device comprising:

a semiconductor substrate having a pattern area and a non-pattern area;

a conductor pattern formed on said pattern area of said semiconductor substrate;

a plurality of dummy patterns formed on said non-pattern area of said semiconductor substrate;

an insulating film formed on said conductive pattern and said plurality of dummy patterns;

wherein said insulating film is formed by a chemical vapor deposition and is smoothed by chemical mechanical polishing;

wherein each of said plurality of dummy patterns are formed in a plurality of dummy areas, each of said plurality of dummy areas having a same shape, and each of said plurality of dummy patterns being arranged in a matrix with predetermined spacing;

wherein each of said dummy patterns has a space portion within each of the dummy areas so that a pattern ratio of said semiconductor device is reduced; ~~and~~

wherein each of said dummy patterns includes an opening at the space portion, the opening having a shape of a letter or a number, each opening of said dummy patterns having a width less than 72 μm; and

wherein the openings of the dummy patterns each have a shape different from one another.

15. (Previously Presented) A semiconductor device according to claim 14, wherein each of said dummy patterns has a rectangular outline.

16-17. (Cancelled)

18. (Currently Amended) A semiconductor device according to claim 15, wherein ~~the~~

each opening has a shape of a plurality of letters.

19-24. (Cancelled)

25. (Previously Presented) A method of manufacturing the semiconductor device of claim 14, the method comprising:

forming the conductor pattern and the dummy patterns above the semiconductor substrate;

forming the insulating film on the conductor pattern and the dummy patterns by chemical vapor deposition, the opening of each dummy pattern being filled by the insulating film; and

smoothing the insulating film by chemical mechanical polishing.

26-29. (Cancelled)

30. (Previously Presented) The method according to claim 25, wherein the insulating film is Boro Phospho Silicate Glass (BPSG) oxide film.

31. (Previously Presented) The method according to claim 25, wherein the insulating film is High Density Plasma-Chemical Vapor Deposition (HDP-CVD) oxide film.